IN THE SPECIFICATION

Please replace paragraph at page 9, lines 3-12, with the following rewritten paragraph:

In a burn-in test on the other hand, it takes a long time to individually conduct electrical inspection of a great number of integrated circuit devices because each integrated circuit device that is an object of inspection is fine, and its handling is inconvenient, whereby inspection cost becomes considerably high. From such reasons, there has been proposed a WLBI (Wafer ~~Lebel~~ Level Burn-in) test in which the burn-in test is collectively performed on a great number of integrated circuits formed on a wafer in the state of the wafer.

Please replace paragraph at page 96, line 3, to page 97, line 14, with the following rewritten paragraph:

The elastic anisotropically conductive films of the anisotropically conductive ~~sheets~~ connectors thus obtained will be described specifically. The total number of the elastic anisotropically conductive films in the anisotropically conductive connector is 393, and each of the elastic anisotropically conductive films has dimensions of 6,000 μm in the lateral direction and 1,200 μm in the vertical direction. Fifty conductive parts for connection are arranged at a pitch of 100 μm in a line in the lateral direction. The dimensions of each of the conductive parts for connection are 40 μm in the lateral direction, 200 μm in the vertical direction and 120 μm in thickness. Conductive parts for non-connection are arranged between the conductive parts for connection located most outside in the lateral direction and the frame plate. The dimensions of each of the conductive parts for non-connection are 40 μm in the lateral direction, 200 μm in the vertical direction and 120 μm in thickness. The projected height of the projected parts formed on the conductive parts for connection is 25 μm in each surface, and each projected part has dimensions of 60 μm in the lateral direction and 210 μm in the vertical direction. The projected height of the projected parts formed on

the conductive parts for non-connection is 25 μm in each surface, and each projected part has dimensions of 90 μm in the lateral direction and 260 μm in the vertical direction. Accordingly, a sum total of areas of end surfaces of the projected parts in all the elastic anisotropically conductive films is 266 mm^2, and a ratio of the sum total of areas of end surfaces of the projected parts in all the elastic anisotropically conductive films to the area of the surface of Wafer W1 for evaluation on a side that the electrodes to be inspected have been formed is 0.0085. The thickness of the insulating part is 70 μm, and a ratio (T2/T1) of the thickness of the insulating part to the thickness of the conductive parts for connection is 0.58. The thickness (thickness of one of the forked portions) of the part to be supported in each of the elastic anisotropically conductive films is 10 μm.

Please replace paragraph at page 100, line 21, to page 101, line 19, with the following rewritten paragraph:

Wafer W2 for evaluation was mounted in place of Wafer W1 for evaluation on the wafer mounting table, a CCD camera capable of viewing both upper and lower directions, was advanced between the probe member and Wafer W2 for evaluation, and alignment of Wafer W2 for evaluation was conducted to the probe member in accordance with the images of this CCD camera in such a manner that the conductive parts for connection of the anisotropically conductive connector are respectively located right over the electrodes to be inspected of Wafer W2 for evaluation. The CCD camera was then removed from between the probe member and Wafer W2 for evaluation, and the probe member was pressurized downward under a load of 58.95 kg (load applied to every conductive part for connection: 3 g on the average), thereby bringing the elastic anisotropically conductive films of the anisotropically conductive connector into contact under pressure with Wafer W2 for evaluation. An electric resistance between adjoining 2 inspection electrodes in Circuit Board

T for evaluation was successively measured at room temperature (25°C) as an electric resistance (hereinafter referred to as "insulation resistance") between adjoining 2 conductive parts for connection (hereinafter referred to as "pairs of conductive parts") to calculate out a proportion of pairs of conductive parts that the insulation resistance was 10 MΩ or ~~higher~~ lower.

Please replace Table 1 at page 102, with the following rewritten Table 1:

		Proportion of conductive parts for connection that the conduction resistance was lower than 1Ω (%)	Proportion of pairs of conductive parts that the insulation resistance was 10MΩ or ~~higher~~ lower (%)
Examples	Anisotropically Conductive Connector (A1)	100	0
	Anisotropically Conductive Connector (A2)	100	0
	Anisotropically Conductive Connector (A3)	100	0
	Anisotropically Conductive Connector (A4)	100	0
	Anisotropically Conductive Connector (A5)	100	0
	Anisotropically Conductive Connector (A6)	100	0
	Anisotropically Conductive Connector (A7)	100	0
	Anisotropically Conductive Connector (A8)	100	0
	Anisotropically Conductive Connector (A9)	100	0
	Anisotropically Conductive Connector (A10)	100	0
Comparative Examples	Anisotropically Conductive Connector (B1)	100	0
	Anisotropically Conductive Connector (B2)	100	0
	Anisotropically Conductive Connector (B3)	100	0
	Anisotropically Conductive Connector (B4)	100	0
	Anisotropically Conductive Connector (B5)	100	0
	Anisotropically Conductive Connector (B6)	100	0
	Anisotropically Conductive Connector (B7)	100	0.1
	Anisotropically Conductive Connector (B8)	100	0.1
	Anisotropically Conductive Connector (B9)	99.5	0.2
	Anisotropically Conductive Connector (B10)	99.3	0.4

Please replace paragraph at page 105, line 9, to page 106, line 27, with the following rewritten paragraph:

An anisotropically conductive connector was arranged on Circuit Board T for inspection in alignment in such a manner that the conductive parts for connection thereof are located on the respective inspection electrodes of Circuit Board T for inspection, a peripheral portion of the anisotropically conductive connector was bonded to Circuit Board T for inspection with RTV silicone rubber, Sheet-like ~~Probe~~ Connector M was arranged on this anisotropically conductive connector in alignment in such a manner that the back-surface electrode parts thereof are located on the respective conductive parts for connection of the anisotropically conductive connector, and a peripheral portion of Sheet-like Connector M was bonded to Circuit Board T for inspection with RTV silicone rubber to produce a probe member. This probe member was then fixed to a pressurizing plate, and Wafer W3 for test was mounted on a wafer mounting table equipped with an electric heater. A CCD camera capable of viewing both upper and lower directions was advanced between the probe member and Wafer W3 for test, and alignment of Wafer W3 for test was conducted to the probe member in accordance with the images of this CCD camera in such a manner that the front-surface electrode parts of the sheet-like connector are respectively located right over the electrodes to be inspected of Wafer W3 for test. The CCD camera was then removed from between the probe member and Wafer W3 for test, and the probe member was pressurized downward under a load of 158 kg (load applied to every conductive part for connection: 8 g on the average), thereby bringing the elastic anisotropically conductive films of the anisotropically conductive connector into contact under pressure with Wafer [[W4]] W3 for test. The wafer mounting table was then heated to 125°C. After the temperature of the wafer mounting table became stable, an electric resistance between 2 inspection electrodes electrically connected to each other through the anisotropically conductive connector, Sheet-

like Connector M and Wafer W3 for test among the 19,650 inspection electrodes in Circuit Board T for inspection was successively measured to record a conduction resistance of the conductive part for connection in the anisotropically conductive connector, thereby counting the number of conductive parts for connection that the conduction resistance was 1 Ω or higher. Thereafter, the wafer mounting table was left to stand for 1 hour in this state and then cooled to room temperature. Thereafter, the pressure against the probe member was released.

Please cancel the original Abstract at page 115, lines 1-26 in its entirety and insert therefor the following replacement Abstract on a separate sheet as follows: